What is claimed is:

1. A read head for use with an interconnect transmission line having a characteristic impedance of Z_0, the read head comprising:

a tunnel valve device, the tunnel valve device having a device resistance R_T corresponding to a predetermined resistance-area (RA) product; and

a shunt resistance R_S connected in parallel across the tunnel valve device, a value of the shunt resistance being based on the parallel combination of R_T and R_S substantially equaling a predetermined selected value of resistance.

2. The read head according to claim 1, wherein the predetermined selected value of resistance substantially equaling the characteristic impedance Z_0 of the interconnect transmission line.

3. The read head according to claim 1, wherein the predetermined resistance-area (RA) product is about equal to at least about 10 Ohms-μm^2.

4. The read head according to claim 1, wherein the predetermined resistance-area (RA) product is about equal to a value of a resistance-area (RA) product in which a Tunnel Magneto-Resistance (TMR) ratio $\Delta R/R_0$ for the tunnel valve device does not substantially increase for further increase in the value of the resistance-area (RA) product.

5. The read head according to claim 1, wherein the shunt resistance R_S is located on a substrate/slider for the read head.

6. The read head according to claim 1, wherein the shunt resistance R_S is located at an arm electronics module associated with the read head.

7. A disk drive, comprising:

an interconnect transmission line having a characteristic impedance of Z_0; and

a read head having a tunnel valve device and a shunt resistance R_S, the tunnel valve device having a device resistance R_T corresponding to a predetermined resistance-area (RA) product; the shunt resistance R_S being connected in parallel across the tunnel valve device, and a value of the shunt resistance being based on the parallel combination of R_T and R_S substantially equaling a predetermined selected value of resistance.

8. The disk drive according to claim 7, wherein the predetermined selected value of resistance substantially equaling the characteristic impedance Z_0 of the interconnect transmission line.

9. The disk drive according to claim 7, wherein the predetermined resistance-area (RA) product is about equal to at least about 10 Ohms-μm^2.

10. The disk drive according to claim 7, wherein the predetermined resistance-area (RA) product is about equal to a value of a resistance-area (RA) product in which a Tunnel Magneto-Resistance (TMR) ratio $\Delta R/R_0$ for the tunnel valve device does not substantially increase for further increase in the value of the resistance-area (RA) product.

11. The disk drive according to claim 7, wherein the shunt resistance R_S is located on a substrate/slider for the read head.

12. The disk drive according to claim 7, wherein the shunt resistance R_S is located at an arm electronics module associated with the read head.